

SI7342DP-T1-GE3

SI7342DP-T1-GE3 Information





Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



SI7342DP-T1-GE3 Specifications

Manufacturer Part Number	SI7342DP-T1-GE3
Manufacturer	Vishay Siliconix
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	PowerPAK? SO-8
Series	TrenchFET?
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	30V
Current - Continuous Drain (Id) @ 25°C	9A (Ta)
Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Vgs(th) (Max) @ Id	1.8V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	19nC @ 4.5V
Input Capacitance (Ciss) (Max) @ Vds	1900pF @ 15V
Vgs (Max)	±12V
FET Feature	-
Power Dissipation (Max)	1.8W (Ta)
Rds On (Max) @ Id, Vgs	8.25 mOhm @ 15A, 10V
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Surface Mount
Supplier Device Package	PowerPAK? SO-8
Package / Case	PowerPAK? SO-8
	Report errors?

SI7342DP-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE BUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

DISCOVER

SI7342DP-T1-GE3 Payment Methods



SI7342DP-T1-GE3 Shipping Methods



If you have any question about SI7342DP-T1-GE3, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com